

Supplementary data

Synthesis of ZnS/Al₂O₃/TaSe₂ core/shell nanowires using thin Ta metal film precursor

Boris Polyakov^{1}, Kevon Kadiwala¹, Edgars Butanovs^{1,2}, Luize Dipane¹, Annamarija Trausa¹,*

Dmitry Bocharov^{1}, Sergei Vlassov³*

¹Institute of Solid State Physics, University of Latvia, 8 Kengaraga Str., LV-1063 Riga, Latvia

²Institute of Technology, University of Tartu, Nooruse 1, 50411 Tartu, Estonia

³Institute of Physics, University of Tartu, W. Ostwaldi Str. 1, 50412 Tartu, Estonia

*Correspondence: boris.polyakov@cfi.lu.lv (B.P.); bocharov@cfi.lu.lv (D.B.)

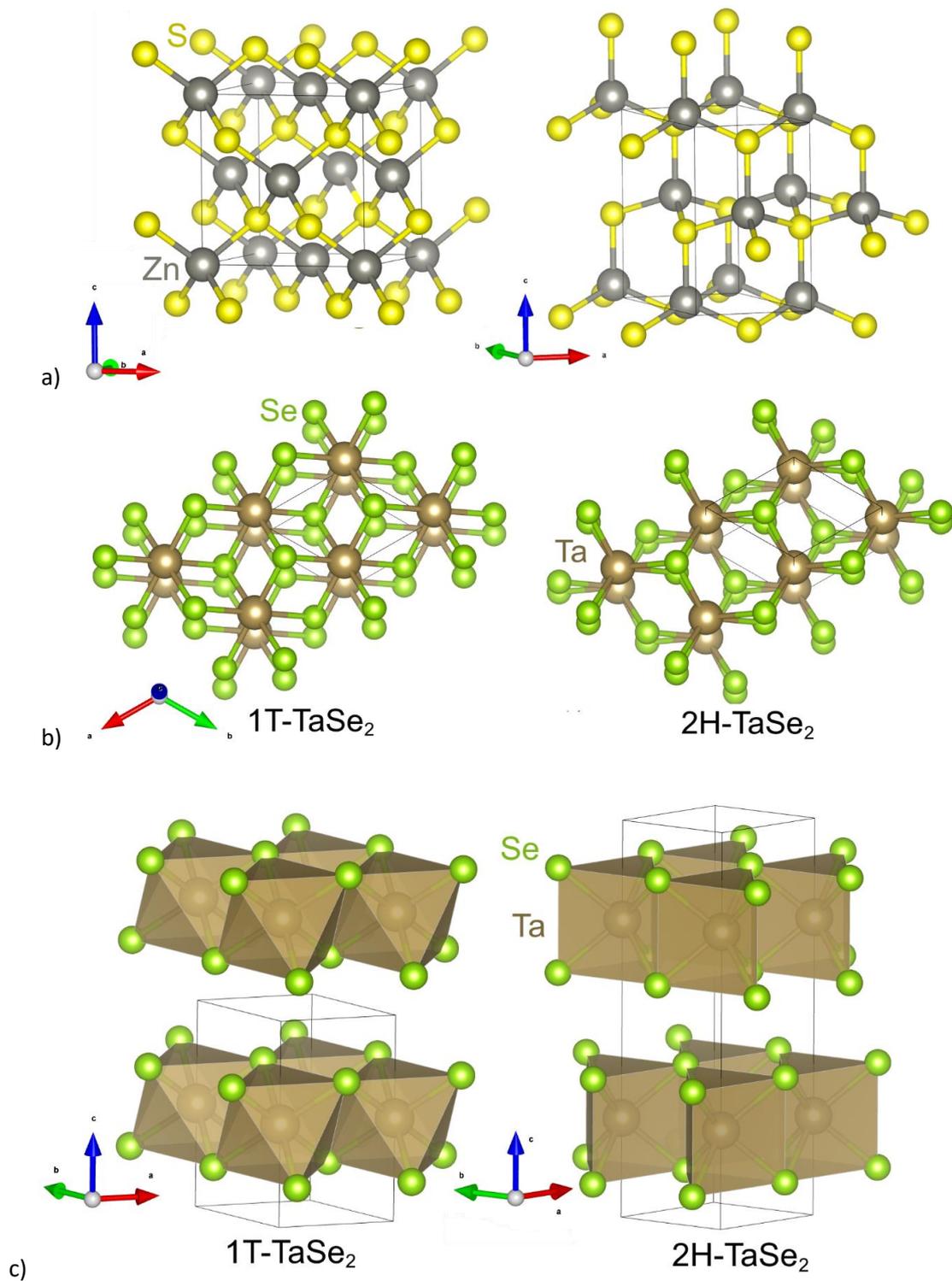


Figure S1. Visual representation of crystal structure of ZnS zincblende (a, left panel) and wurtzite (a, right panel), as well as 1T-TaSe₂ and 2H-TaSe₂ (top view in (b) and side view in (c)). Atomic environment of Se atoms around Ta is shown in (c) for better explanation. Unit cell for each structure is shown with black polyhedral. 1T-TaSe₂ has a trigonal D_{3d} space group symmetry, where each Ta atom is octahedrally coordinated by six Se atoms. 2H-TaSe₂ is a more stable phase and has a D_{6h} space-group symmetry, where each Ta atom is coordinated by six Se atoms in a trigonal prismatic arrangement. For 1T-TaSe₂ cells is doubled in z--direction for better comparison between both phases of TaSe₂.

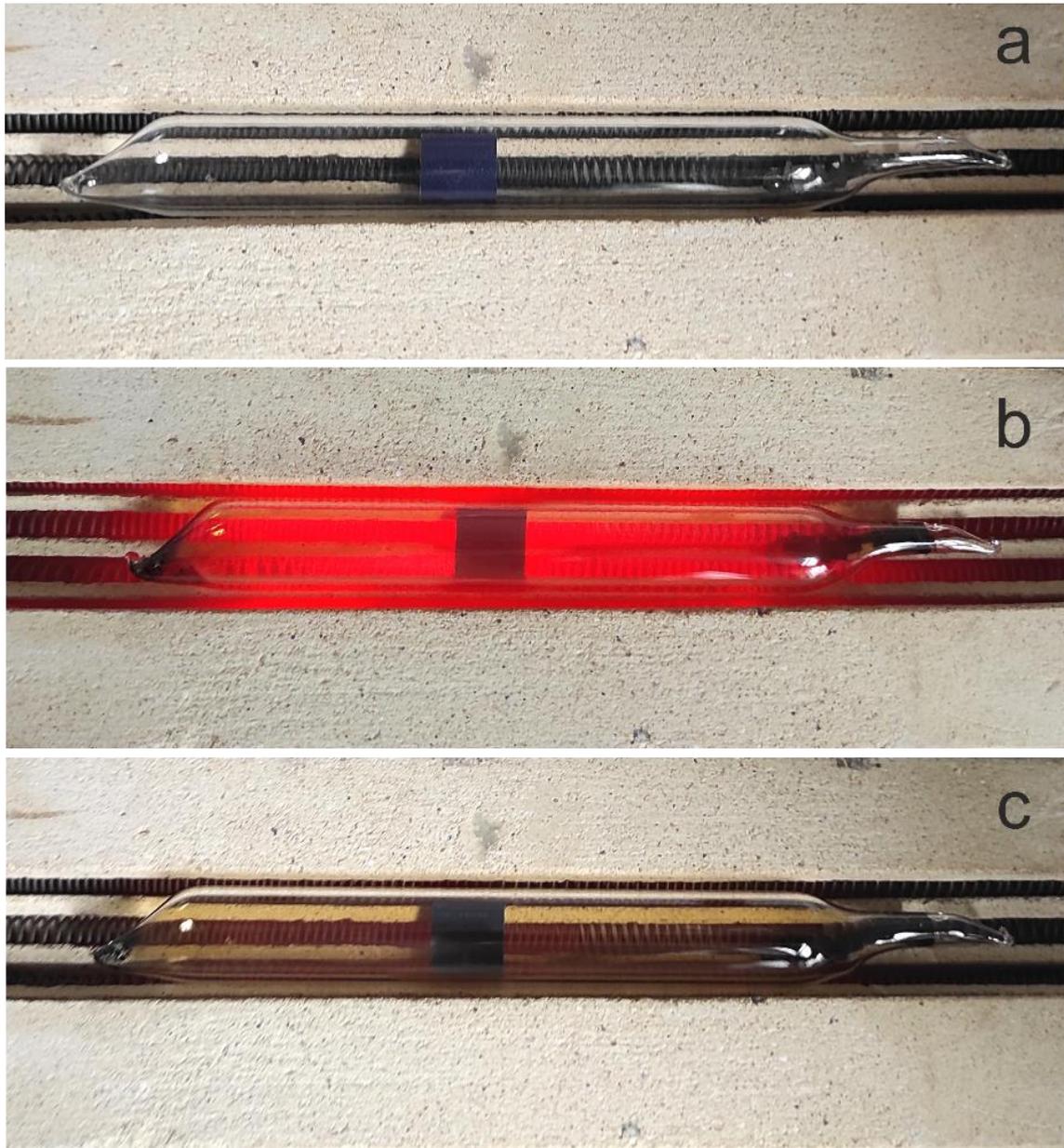


Figure S2. Selenization of Ta thin film and ZnS/Al₂O₃/TaSe₂ NWs on Si/SiO₂ substrate in quartz ampoule. Images before ampoule heating (a), during ampoule heating (b), during cooling (c).

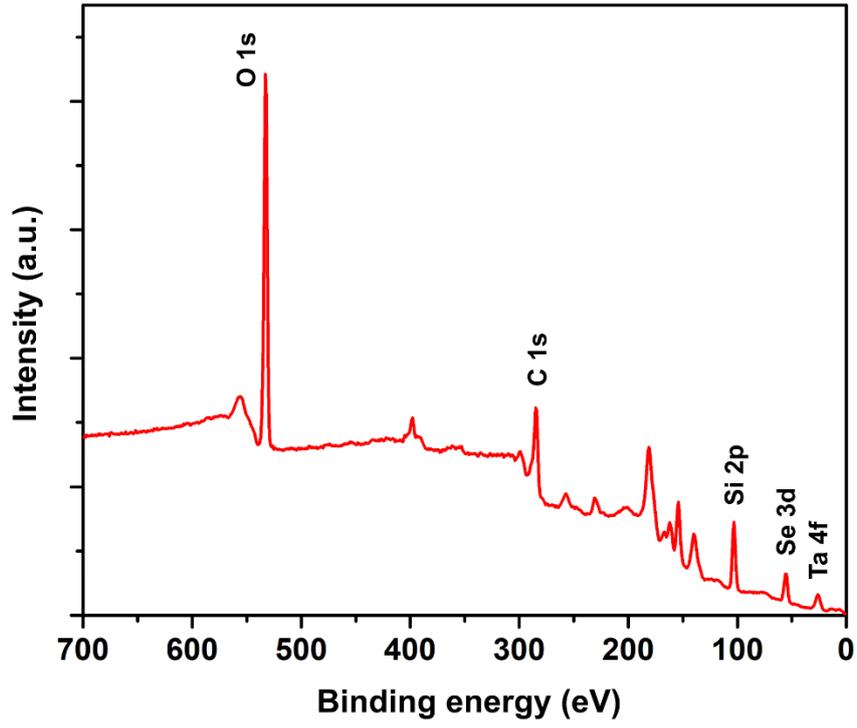


Figure S3. XPS survey scan for ZnS/Al₂O₃/TaSe₂ NWs on Si/SiO₂ substrate. The characteristic peaks of all elements present on the sample surface are marked correspondingly.

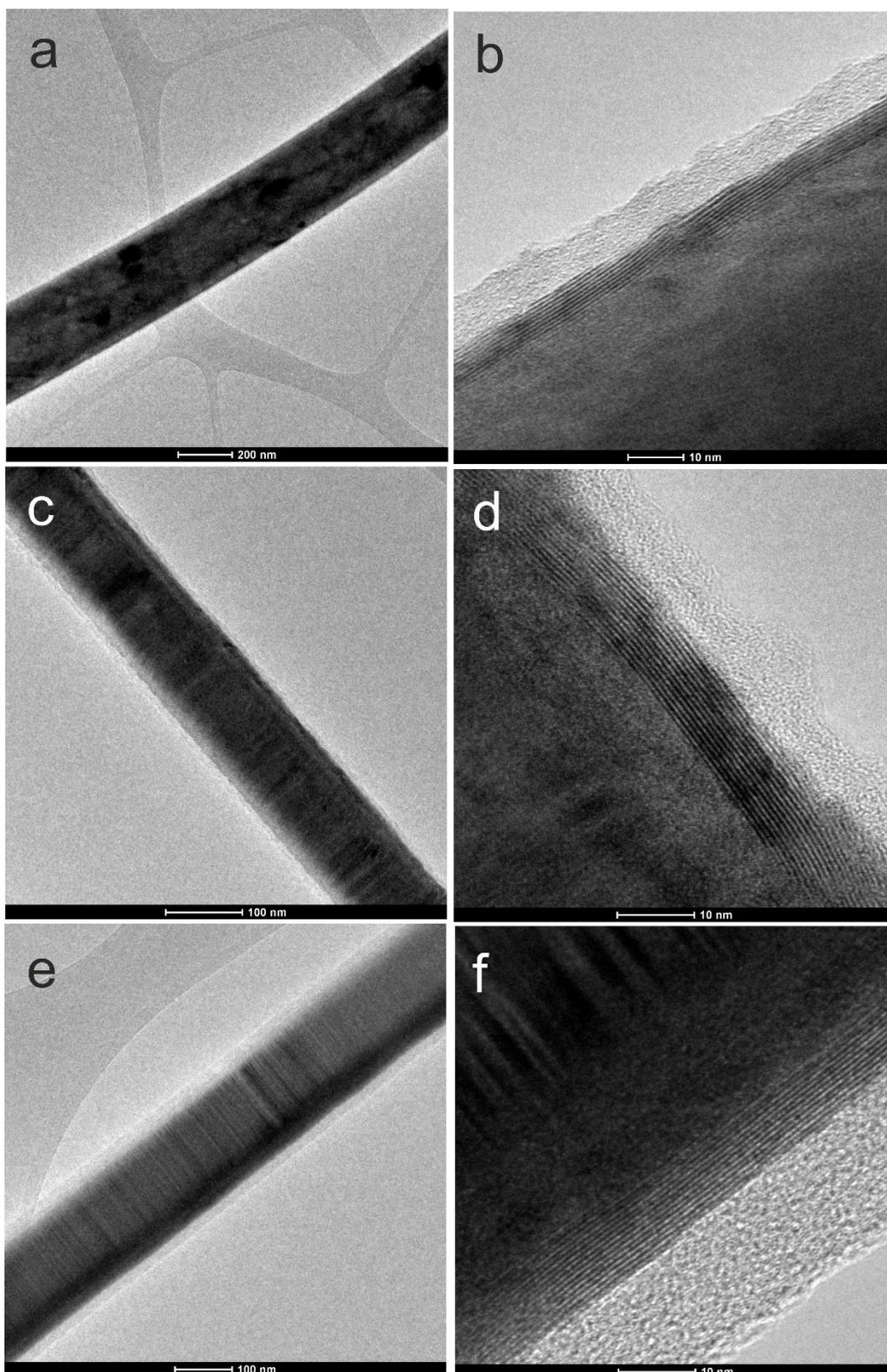


Figure S4. TEM images of ZnS/Al₂O₃/TaSe₂ NWs at low (a, c, e) and high (b, d, f) magnifications.

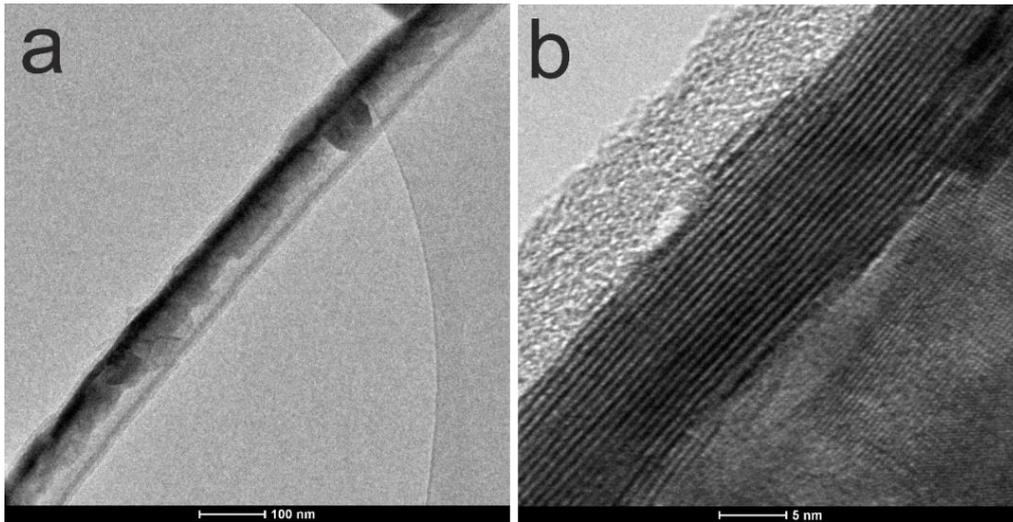


Figure S5. TEM images of ZnO/Al₂O₃/TaSe₂ NWs at low (a) and high (b) magnifications. ZnO NW core was sublimated and TaSe₂ shell cover Al₂O₃ empty “tube”.